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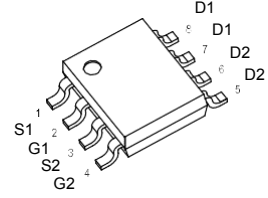


PLED

Product data sheet

Product Summary

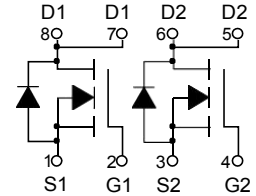
V_{DS}	30V
I_D (at $V_{GS}=10V$)	6A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 30m Ω
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 42m Ω



SOP-8

General Description

The AO4842-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.



N-Channel MOSFET

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		V_{DS}	30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	$T_A=25^\circ\text{C}$	I_D	6	A	
	$T_A=70^\circ\text{C}$		5		
Pulsed Drain Current ^C		I_{DM}	30		
Avalanche Current ^C		I_{AS}, I_{AR}	10	A	
Avalanche energy $L=0.1\text{mH}$ ^C		E_{AS}, E_{AR}	5	mJ	
Power Dissipation ^B	$T_A=25^\circ\text{C}$	P_D	2	W	
	$T_A=70^\circ\text{C}$		1.3		
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		
Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
	Steady-State		74	90	$^\circ\text{C/W}$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	32	40	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.2	1.8	2.4	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =6A T _J =125°C		25 40	30 48	mΩ
		V _{GS} =4.5V, I _D =5A		33	42	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =6A		15		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.76	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		255	310	pF
C _{oss}	Output Capacitance			45		pF
C _{rss}	Reverse Transfer Capacitance			35	50	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.6	3.25	4.9	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =6A		5.2	6.3	nC
Q _{g(4.5V)}				2.55	3.2	nC
Q _{gs}	Gate Source Charge			0.85		nC
Q _{gd}	Gate Drain Charge			1.3		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =2.5Ω, R _{GEN} =3Ω		4.5		ns
t _r	Turn-On Rise Time			2.5		ns
t _{D(off)}	Turn-Off DelayTime			14.5		ns
t _f	Turn-Off Fall Time			3.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =6A, dI/dt=100A/μs		8.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =6A, dI/dt=100A/μs		2.2		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C, using ≤ 10s junction-to-ambient thermal resistance.

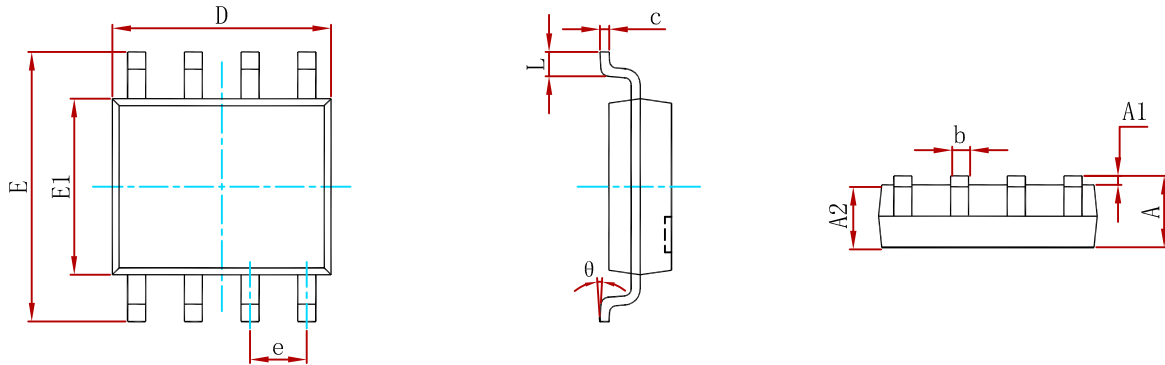
C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

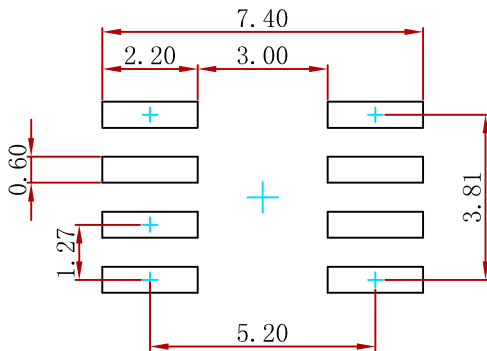
F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150°C. The SOA curve provides a single pulse rating g.

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO4842-MS	SOP-8	3000

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